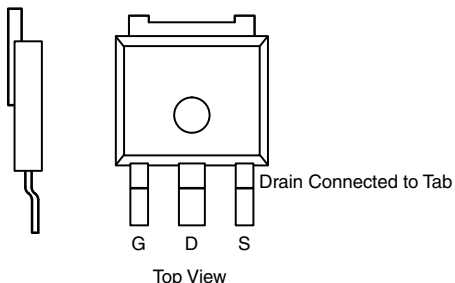


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0038
I _D (A)	50
Configuration	Single

TO-252
Reverse Lead DPAK



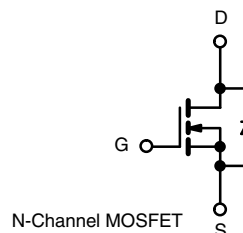
FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912

AUTOMOTIVE
GRADE



RoHS
COMPLIANT
HALOGEN
FREE



N-Channel MOSFET

ORDERING INFORMATION

Package	TO-252 Reverse Lead DPAK
Lead (Pb)-free and Halogen-free	SQR50N04-3m8-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current ^a	I _D	50	A
		50	
Continuous Source Current (Diode Conduction) ^a	I _S	50	
Pulsed Drain Current ^b	I _{DM}	200	
Single Pulse Avalanche Current	I _{AS}	62	
Single Pulse Avalanche Energy	E _{AS}	192	mJ
Maximum Power Dissipation ^b	P _D	136	W
		45	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R _{thJA}	50	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3.0	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A	-	0.0030	0.0038	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0064	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0076	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		-	120	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	5360	6700	pF
Output Capacitance	C _{oss}			-	500	627	
Reverse Transfer Capacitance	C _{rss}			-	250	310	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 50 A	-	70	105	nC
Gate-Source Charge ^c	Q _{gs}			-	16	-	
Gate-Drain Charge ^c	Q _{gd}			-	13	-	
Gate Resistance	R _g	f = 1 MHz		0.9	1.9	2.9	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.4 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 1 Ω		-	11	16	ns
Rise Time ^c	t _r			-	5	8	
Turn-Off Delay Time ^c	t _{d(off)}			-	34	51	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	A
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.9	1.5	V

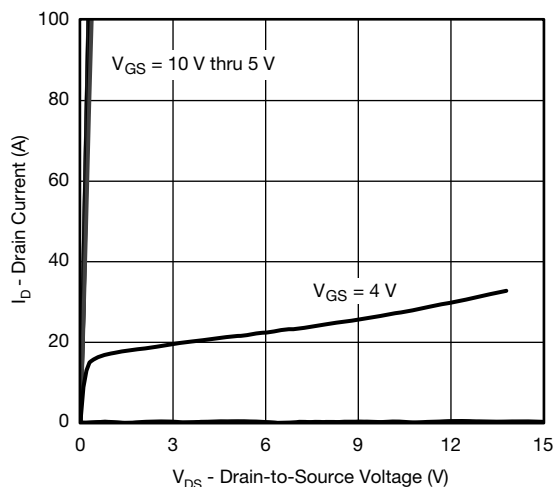
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

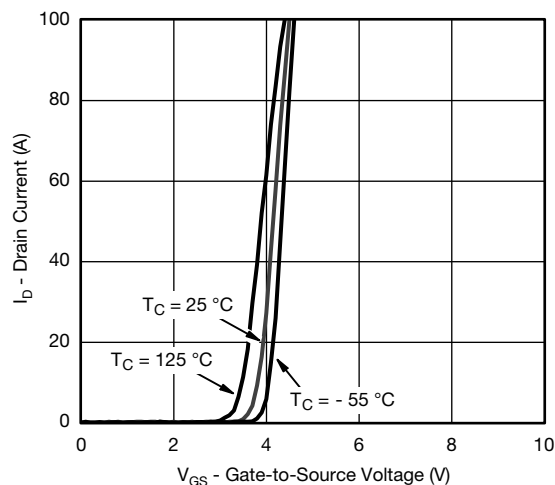
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



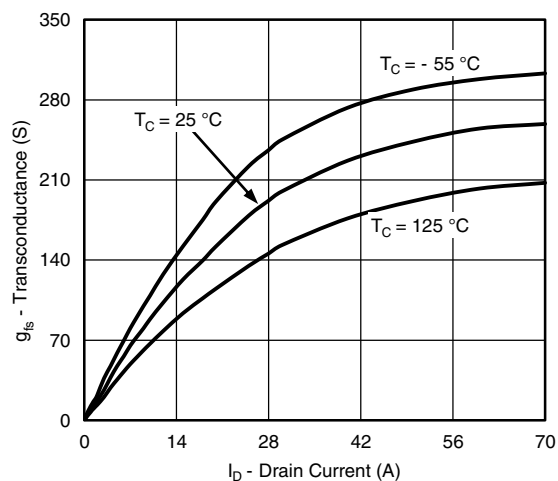
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



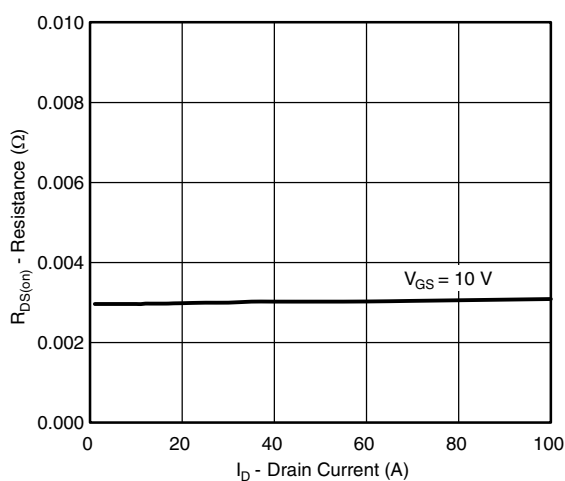
Output Characteristics



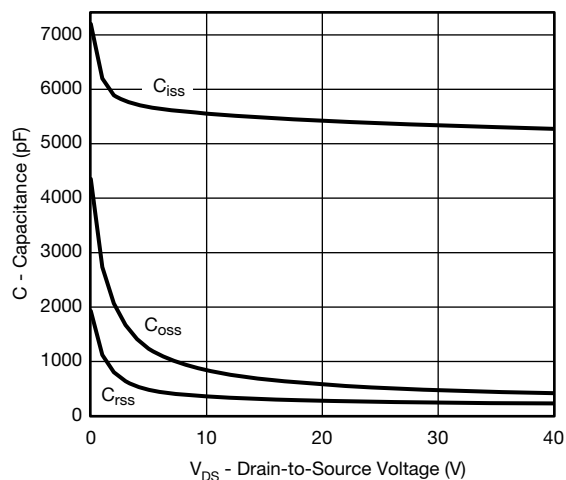
Transfer Characteristics



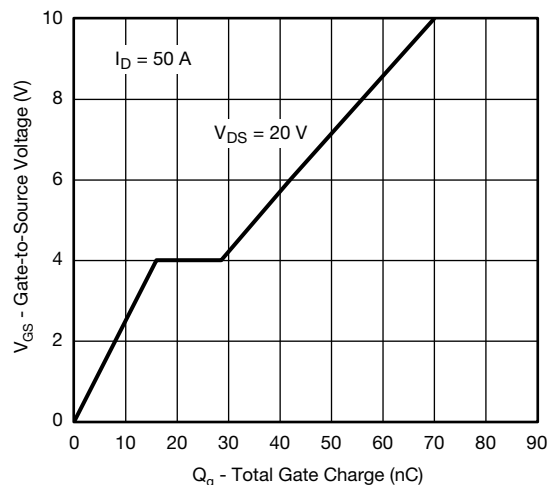
Transconductance



On-Resistance vs. Drain Current



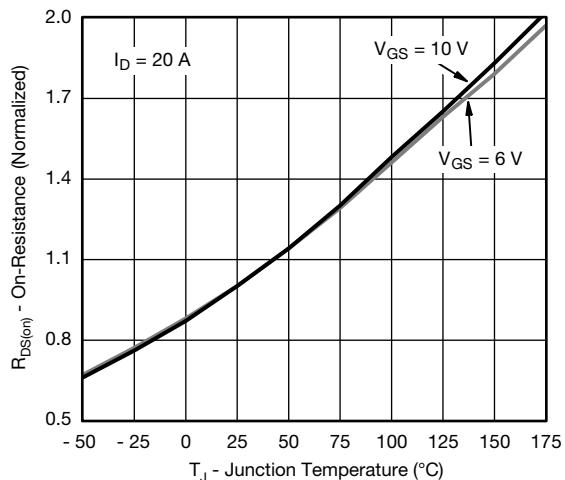
Capacitance



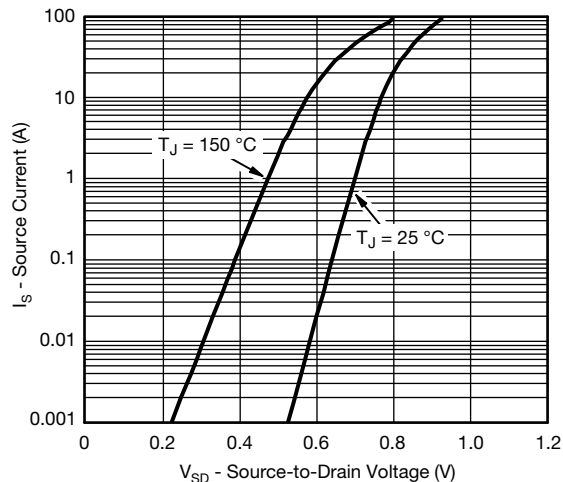
Gate Charge



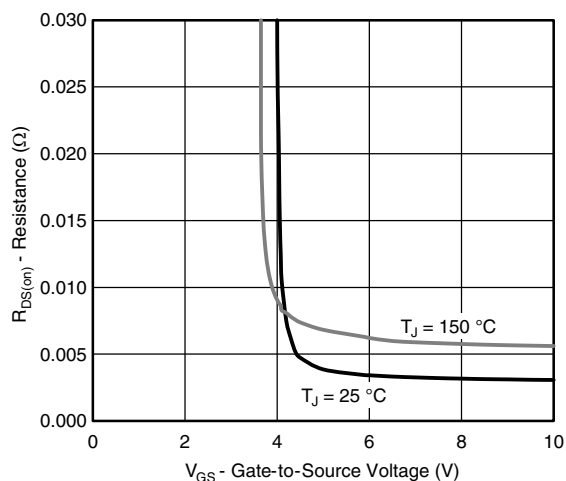
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



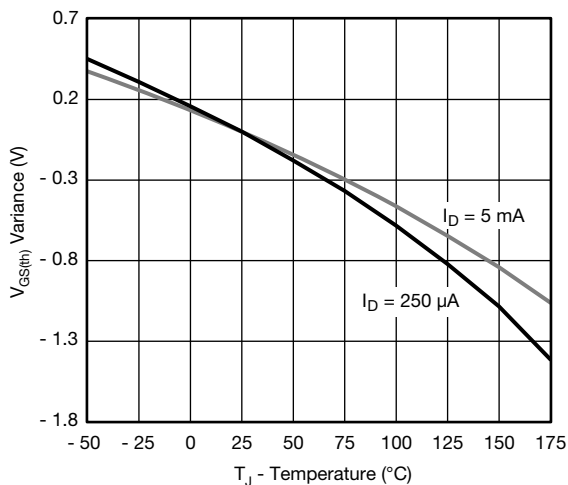
On-Resistance vs. Junction Temperature



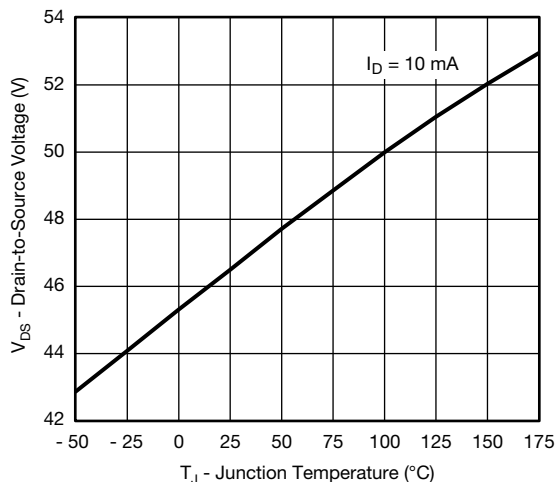
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



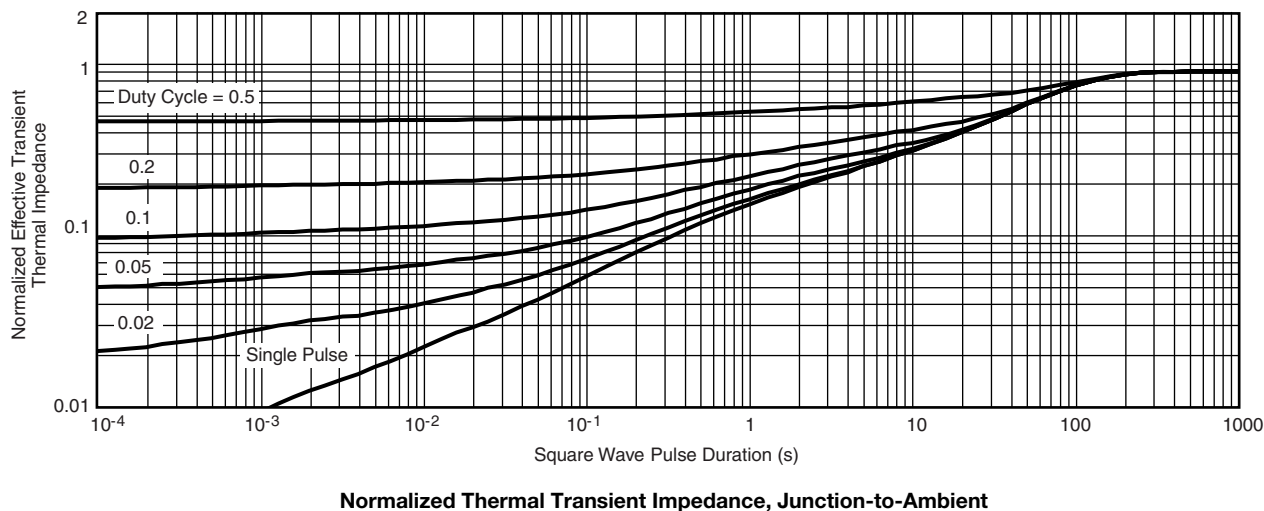
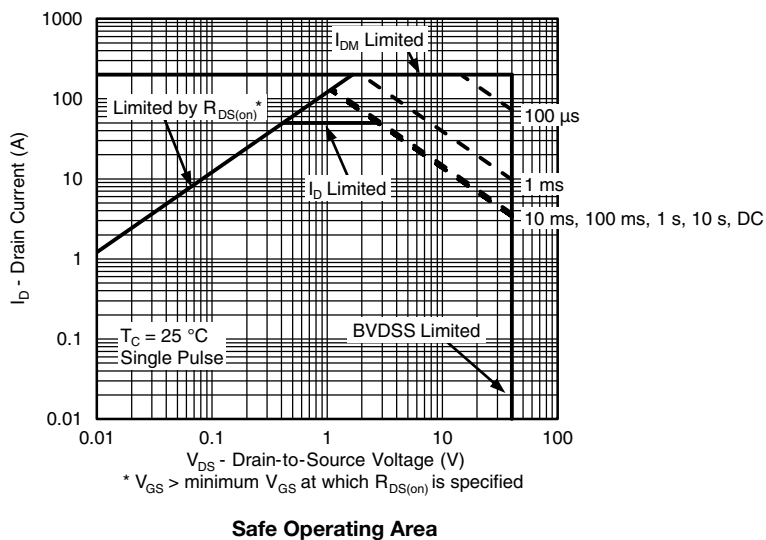
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

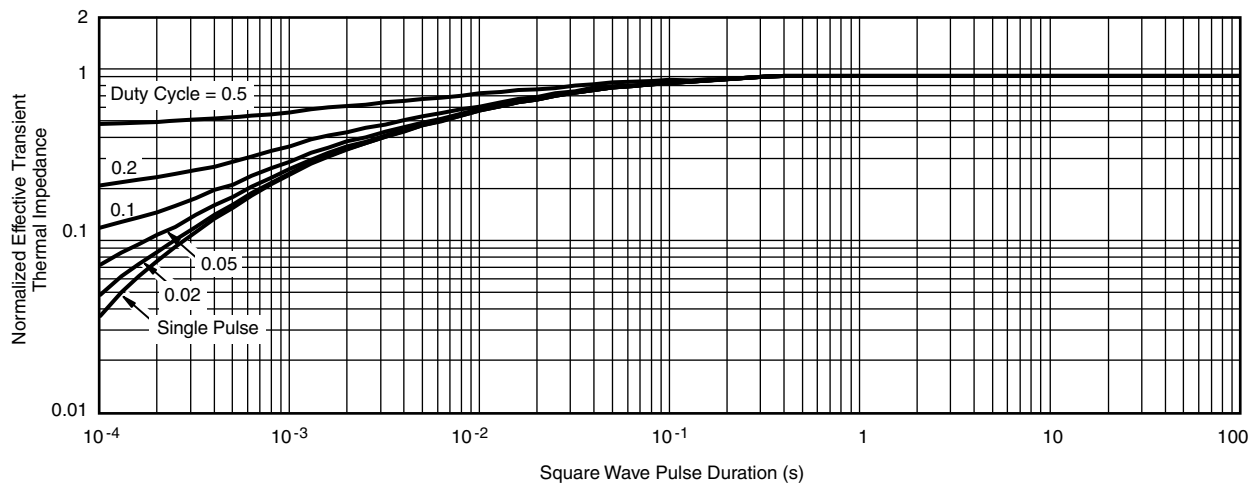


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



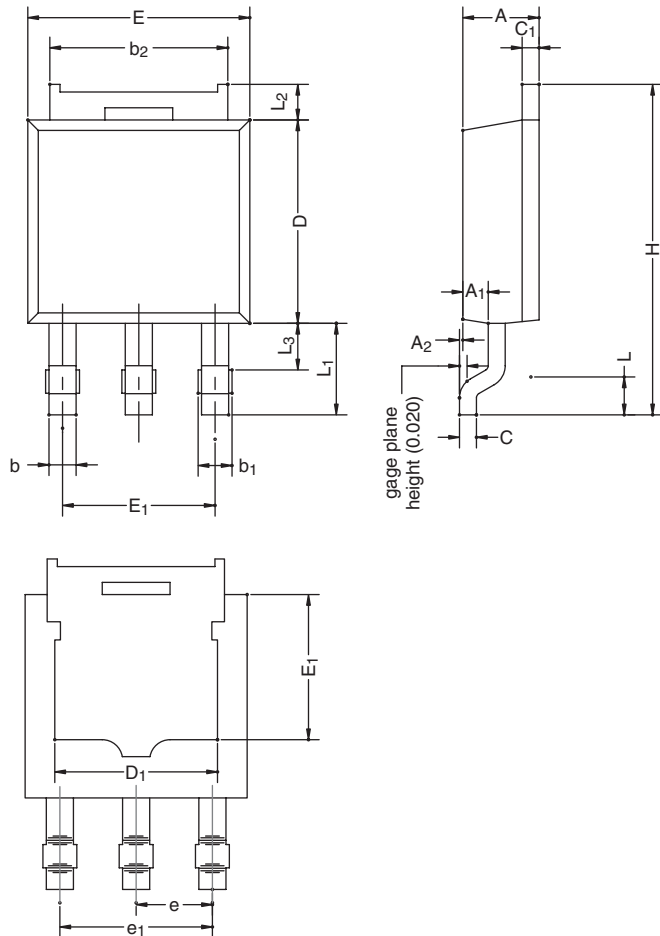
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-252 REVERSE LEAD CASE OUTLINE



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.23	2.33	0.088	0.092
A ₁	0.64	0.89	0.025	0.035
A ₂	0.03	0.23	0.001	0.009
b	0.71	0.88	0.028	0.035
b ₁	0.76	1.14	0.030	0.045
b ₂	5.23	5.44	0.206	0.214
C	0.46	0.58	0.018	0.023
C ₁	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D ₁	4.49	5.00	0.177	0.197
E	6.48	6.73	0.255	0.265
E ₁	4.32	-	0.170	-
e	2.28 BSC		0.090 BSC	
e ₁	4.57 BSC		0.180 BSC	
H	9.65	10.41	0.380	0.410
L	1.40	1.78	0.055	0.070
L ₁	2.74 BSC		0.108 BSC	
L ₂	0.89	1.27	0.035	0.050
L ₃	1.15	1.52	0.040	0.060
ECN: T-08706-Rev. B, 29-Sep-08				
DWG: 5894				

Note

Dimension L₃ for reference only.



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